

# RGTV60TS65

## 650V 30A Field Stop Trench IGBT

$V_{CES}$	650V
I <sub>C(100°C)</sub>	30A
V <sub>CE(sat) (Typ.)</sub>	1.5V
$P_D$	194W

### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating; RoHS Compliant

## Applications

Solar Inverter

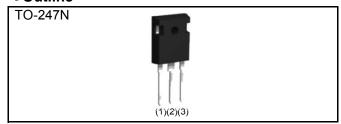
**UPS** 

Welding

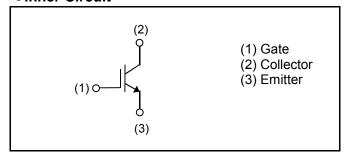
ΙH

**PFC** 

### Outline



### ●Inner Circuit



### Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	ı
Typo	Tape Width (mm)	ı
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTV60TS65

## ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		$V_{CES}$	650	V	
Gate - Emitter Voltage		$V_{GES}$	±30	V	
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	60	А	
	T <sub>C</sub> = 100°C	I <sub>C</sub>	30	А	
Pulsed Collector Current		I <sub>CP</sub> *1	120	А	
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	194	W	
	T <sub>C</sub> = 100°C	P <sub>D</sub>	97	W	
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C	
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C	

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

### ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.77	°C/W

# ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i i e te i	Syllibol		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	ı	V
Collector Cut - off Current	I <sub>CES</sub>	V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V	1	-	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 21.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage		I <sub>C</sub> = 30A, V <sub>GE</sub> = 15V				
	V <sub>CE(sat)</sub>	T <sub>j</sub> = 25°C	-	1.5	1.9	V
		T <sub>j</sub> = 175°C	-	1.85	-	

# ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Darameter	Cymphal	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	$C_{\text{ies}}$	V <sub>CE</sub> = 30V	-	1730	-	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V	-	74	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	30	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 400V	-	64	-	
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 30A	-	14	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	24	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	-	33	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	12	-	20
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 25°C	-	105	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	40	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	0.57	-	
Turn - off Switching Loss	$E_{off}$	reverse recovery	-	0.50	-	mJ
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	-	32	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	13	-	20
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 175°C	-	121	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	80	-	
Turn - on Switching Loss	E <sub>on</sub>	*E <sub>on</sub> includes diode	-	0.63	-	m l
Turn - off Switching Loss	E <sub>off</sub>	reverse recovery	-	0.72	-	mJ
		I <sub>C</sub> = 120A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				
		V <sub>CC</sub> ≤ 360V				
Short Circuit Withstand Time	$t_{sc}$	V <sub>GE</sub> = 15V	2	-	-	μs
		T <sub>j</sub> = 25°C				

### **•**Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

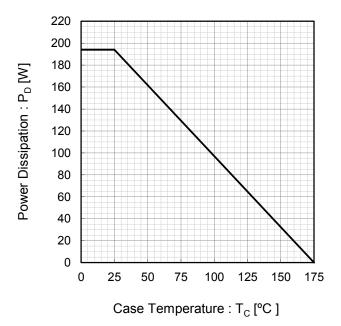


Fig.2 Collector Current vs. Case Temperature

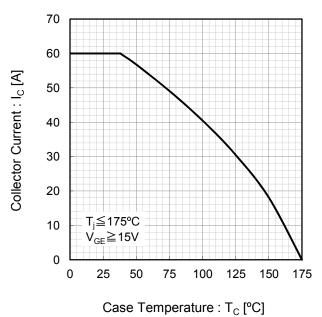


Fig.3 Forward Bias Safe Operating Area

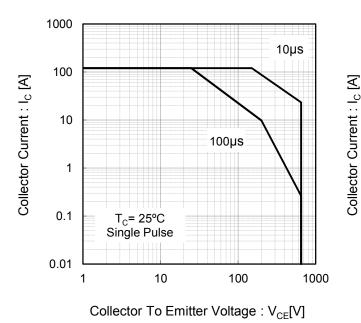
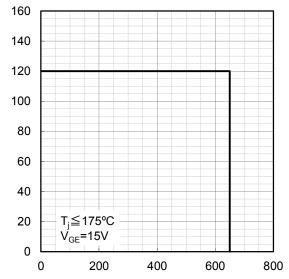


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

### • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

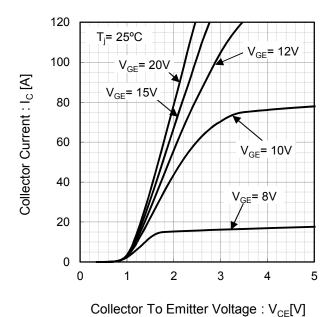
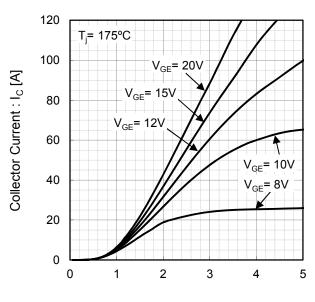


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

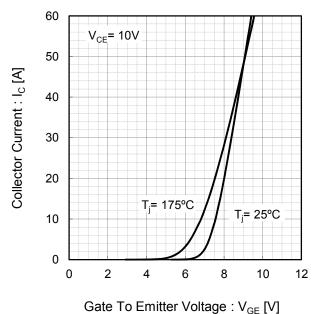
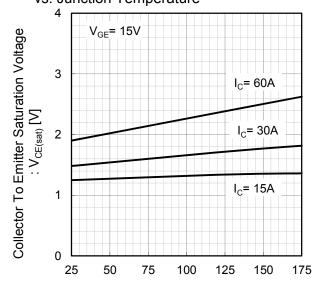


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

### Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

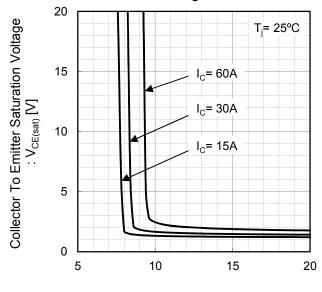
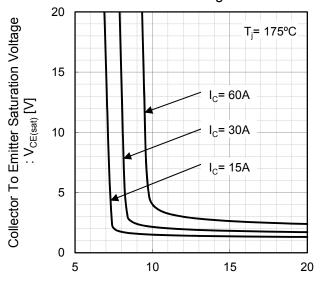


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage :  $V_{GE}[V]$ 

Gate To Emitter Voltage : V<sub>GE</sub> [V]

vs. Collector Current

1000

t<sub>d(off)</sub>

t<sub>d(on)</sub>

Fig.11 Typical Switching Time

Collector Current : I<sub>C</sub> [A]

30

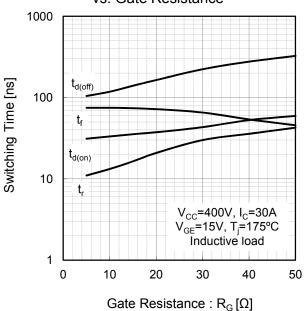
 $V_{CC}$ =400V,  $V_{GE}$ =15V R<sub>G</sub>=10 $\Omega$ , T<sub>j</sub>=175°C Inductive load

40

50

60

Fig.12 Typical Switching Time vs. Gate Resistance



Switching Time [ns]

10

0

10

20

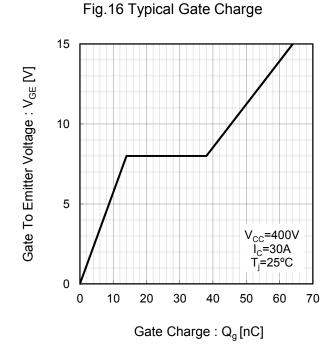
### • Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 Eoff 0.1 V<sub>CC</sub>=400V, V<sub>GE</sub>=15V R<sub>G</sub>=10Ω, T<sub>j</sub>=175°C Inductive load 0.01 40 0 20 50 10 30 60 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 Eon 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=30A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

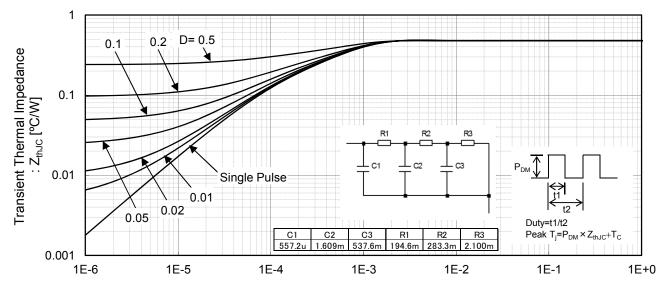
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]



### **•**Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



Pulse Width: t1[s]

## ●Inductive Load Switching Circuit and Waveform

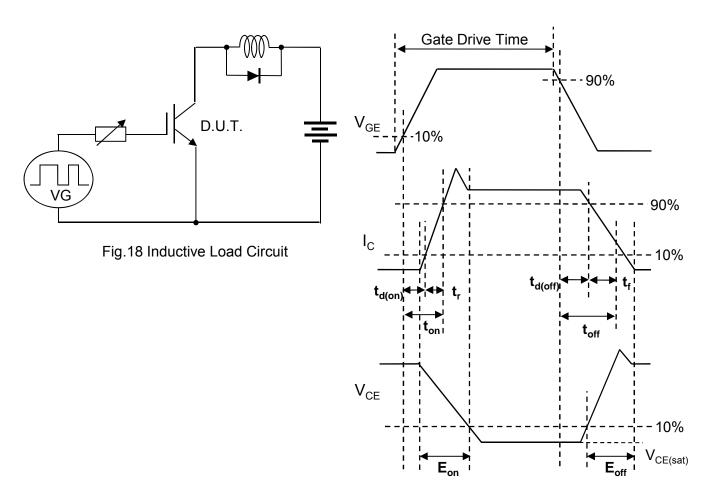


Fig.19 Inductive Load Waveform

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